

IN THE SPECIFICATION:

Please replace paragraph number [0001] with the following rewritten paragraph:

[0001] This application is a continuation of application Serial No. 09/809,720, filed March 15, 2001, pending now U.S. Patent 6,599,660, issued July 29, 2003.

Please replace paragraph number [0009] with the following rewritten paragraph:

[0009] The electromagnetic intensity represented by the second curve components 26a, 26b is also known as “ringing effects,” and one significant disadvantage of APSMs is that such ringing effects become much more severe as feature density of an APSM increases. As device features designed into an APSM are spaced closer and closer together, the ringing effects of adjacent device features begin to overlap, and as the ringing effects overlap, the electromagnetic intensity of such ringing effects becomes additive. These increased ringing effects are known as “additive side lobes”, “additive ringing effects”, or “proximity effects.” In contrast to isolated ringing effects produced by isolated device features, the electromagnetic intensity of additive side lobes created by closely-spaced (i.e., $\leq 0.5 \mu\text{m}$) or nested device features often becomes sufficiently intense to cause printing of the resist layer, which is commonly termed “side lobe printing.”

Please replace paragraph number [0053] with the following rewritten paragraph:

[0053] The first attenuating layer 100 is only slightly attenuating, allowing about 12% to about 20% transmission. Moreover, the first attenuating layer 100 may be formed such that the first attenuating layer 100 induces a one hundred eighty degree (180°) phase shift in radiation passing through the first attenuating layer 100. Alternatively, the first etch stop layer 102 may be formed to induce a one hundred eighty degrees (180°) phase shift, while the first attenuating layer 100 serves only to attenuate passing radiation, or the first attenuating layer 100 and first etch stop layer 102 may be formed such that radiation must pass through both layers 100, 102 to be shifted one hundred eighty degrees (180°) out of phase. Where the first attenuating layer 100

is formed such that the first attenuating layer 100 ~~layer~~ both attenuates passing radiation and shifts the passing radiation one hundred eighty degree (180°) out of phase, the first etch stop layer 102 is formed to allow passage of radiation without inducing any further phase shifts.